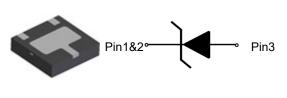


### Description

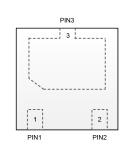
The XT3P30VU diode is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebooks, and PDA's. It offers superior electrical characteristics such as low clamping voltage, low leakage current and high surge capability. It is designed to protect sensitive electronic components which are connected to power lines, from over-stress caused by ESD (Electrostatic Discharge), EFT (Electrical Fast Transients) and Lightning.

The XT3P30VU is in a DFN2020-3L package and will protect one unidirectional line. It may be used to provide ESD protection up to  $\pm$ 30kV (Contact and air discharge) according to IEC61000-4-2, and withstand peak pulse current up to 180A (8/20µs) according to IEC61000-4-5.

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#### DFN2020-3L



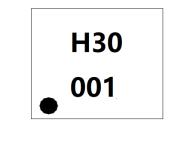
# Pin Configuration (Bottom View)



- Working voltage: 30V
- DFN2020-3L Package
- ♦ 7000 Watts peak pulse power (t<sub>p</sub>=8/20us)
- ◆ Transient protection for data lines to IEC 61000-4-2 (ESD) ±30kV (air), ±30kV (contact)
  IEC 61000-4-5 (Surge)180A (8/20us)
  IEC61000-4-4 (EFT) 40A (5/50ns)
- Low leakage current
- Low clamping voltage
- Solid-state silicon-avalanche technology

## Applications

- Power lines
- Personal digital assistants (PDA's)
- Microprocessors based equipment
- Notebooks, Desktops, and Servers
- Cell phone Handsets and Accessories
- Portable Electronics
- Peripherals



Marking

## **Order Information**

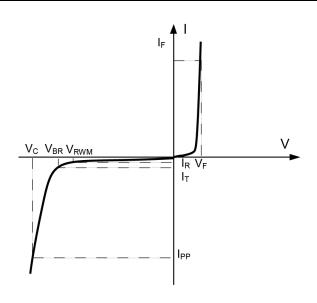
Device	Package	Shipping
XT3P30VU	DFN2020-3L	3000/Tape&Reel

1



## **Definitions of electrical characteristics**

Symbol	Parameter	
V <sub>RWM</sub>	Reverse Stand-off Voltage	
IR	Reverse Leakage Current @ V <sub>RWM</sub>	
VBR	Reverse Breakdown Voltage @ I⊤	
Ι <sub>Τ</sub>	Test Current	
IPP	Reverse Peak Pulse Current	
Vc	Clamping Voltage @ IPP	
lF	Forward Current	
VF	Forward Voltage @ I⊧	
Cj	Junction Capacitance	
IPP	Peak Pulse Current	



# Absolute Maximum Rating

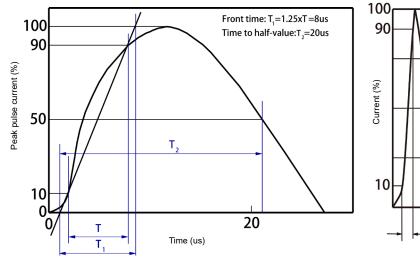
Rating	Symbol	Value	Units
Peak Pulse Power ( $t_P = 8/20\mu S$ )	Ррк	7000	W
Peak Pulse Current (8/20 µ s)	I <sub>pp</sub>	180	A
ESD according to IEC61000-4-2 air discharge	Vesd	±30	kV
ESD according to IEC61000-4-2 contact discharge	VESD	±30	kV
Operating Temperature	Тор	-55 to +125	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C

# Electrical Characteristics (Ta=25°C, unless otherwise noted)

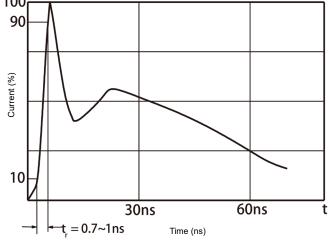
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Reverse Stand-off Voltage	V <sub>RWM</sub>				30	V
Reverse Breakdown Voltage	V <sub>BR</sub>	I⊤ = 1mA	31		35	V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> =30V			0.5	μA
Clamping Voltage	Vc	I <sub>PP</sub> =180A t <sub>P</sub> = 8/20µs		38	42	V
Junction Capacitance	Cj	V <sub>R</sub> =0V f = 1MHz		550		pF



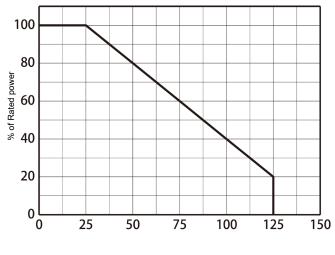
# Typical Characteristics (Ta=25℃, unless otherwise noted)



8/20 us waveform per IEC61000-4-5



Contact discharge current waveform per IEC61000-4-2

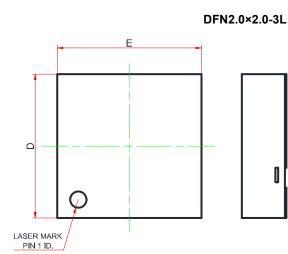


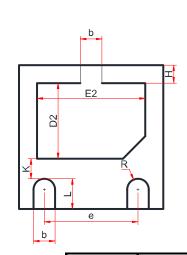
 $T_A$  - Ambient temperature (°C )

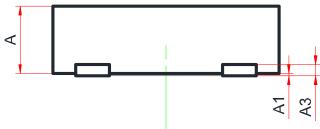
Non-repetitive peak pulse power vs. Pulse time



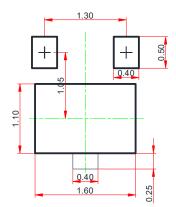
## Package Outline Dimensions (DFN2020-3L)







#### **Recommend Land Pattern (Unit: mm)**



Symbol	Binensions in Minimeters			
Symbol	Min.	Тур.	Max.	
А	0.51	0.55	0.60	
A1	0.00	0.02	0.05	
A3	0.15 REF.			
b	0.25	0.30	0.35	
D	1.90	2.00	2.10	
E	1.90	2.00	2.10	
D2	0.85	1.00	1.10	
E2	1.35	1.50	1.60	
е	1.20	1.30	1.40	
Н	0.20	0.25	0.30	
К	0.20	0.30	0.40	
L	0.35	0.40	0.45	
R	0.15	-	-	

**Dimensions In Millimeters** 

#### Note:

This recommended land pattern is for reference purpose only.

#### NOTICE

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